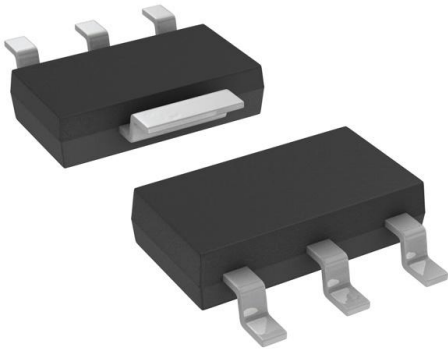


# NSV60601MZ4T3G Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NSV60601MZ4T3G-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	NSV60601MZ4T3G
Description	TRANS NPN 60V 6A SOT223
Detailed Description	Bipolar (BJT) Transistor NPN 60 V 6 A 100MHz 800 mW Surface Mount SOT-223 (TO-261)



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

NSV60601MZ4T3G

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

60 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

800 mW

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

TO-261-4, TO-261AA

Base Product Number:

NSV60601

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

6 A

Vce Saturation (Max) @ Ib, Ic:

300mV @ 600mA, 6A

DC Current Gain (hFE) (Min) @ Ic, Vce:

120 @ 1A, 2V

Frequency - Transition:

100MHz

Mounting Type:

Surface Mount

Supplier Device Package:

SOT-223 (TO-261)

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



# NSS60601MZ4

## Low $V_{CE(sat)}$ Transistor, NPN, 60 V, 6.0 A

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*
- Complementary to NSS60600MZ4

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	Vdc
Collector-Base Voltage	$V_{CBO}$	100	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	6.0	A
Collector Current - Peak	$I_{CM}$	12.0	A

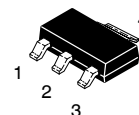
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



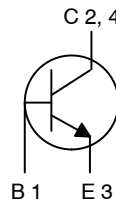
**ON Semiconductor**<sup>®</sup>

<http://onsemi.com>

**60 VOLTS, 6.0 AMPS  
2.0 WATTS  
NPN LOW  $V_{CE(sat)}$  TRANSISTOR  
EQUIVALENT  $R_{DS(on)} 50 \text{ m}\Omega$**

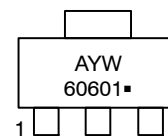


**SOT-223  
CASE 318E  
STYLE 1**



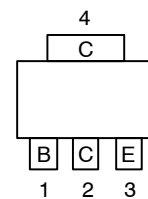
**Schematic**

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
60601 = Specific Device Code  
▪ = Pb-Free Package

### PIN ASSIGNMENT



**Top View Pinout**

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**NSS60601MZ4****THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 1)	800 6.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	155	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 2)	2 15.6	W mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	64	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec.)	$P_{D\text{single}}$ (Note 3)	710	mW
Junction and Storage Temperature Range	$T_J, T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

- FR-4 @  $7.6 \text{ mm}^2$ , 1 oz. copper traces.
- FR-4 @  $645 \text{ mm}^2$ , 1 oz. copper traces.
- Thermal response.

**ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NSS60601MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSV60601MZ4T1G*	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSS60601MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel
NSV60601MZ4T3G*	SOT-223 (Pb-Free)	4,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**NSS60601MZ4****ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	60	–	–	Vdc
Collector – Base Breakdown Voltage ( $I_C = 0.1\text{ mA}$ , $I_E = 0$ )	$V_{(BR)CBO}$	100	–	–	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 0.1\text{ mA}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	–	Vdc
Collector Cutoff Current ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	–	0.1	$\mu\text{A}$ dc
Emitter Cutoff Current ( $V_{EB} = 6.0\text{ Vdc}$ )	$I_{EBO}$	–	–	0.1	$\mu\text{A}$ dc

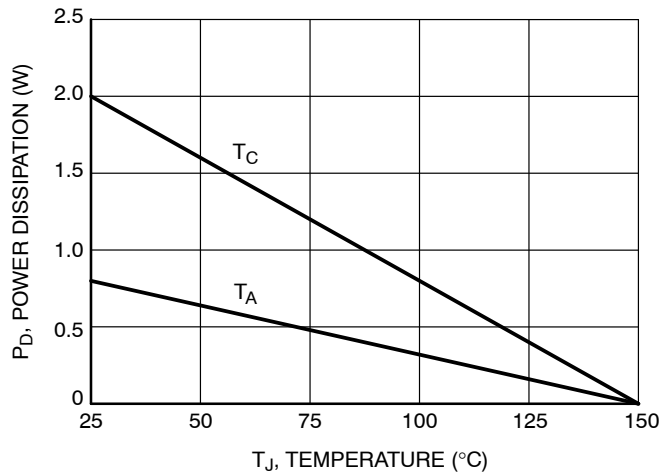
**ON CHARACTERISTICS**

DC Current Gain (Note 4) ( $I_C = 500\text{ mA}$ , $V_{CE} = 2.0\text{ V}$ ) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ ) ( $I_C = 2.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ ) ( $I_C = 6.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ )	$h_{FE}$	150 120 100 50	– – – –	– 360 – –	–
Collector – Emitter Saturation Voltage (Note 4) ( $I_C = 0.1\text{ A}$ , $I_B = 2.0\text{ mA}$ ) ( $I_C = 1.0\text{ A}$ , $I_B = 0.100\text{ A}$ ) ( $I_C = 2.0\text{ A}$ , $I_B = 0.200\text{ A}$ ) ( $I_C = 3.0\text{ A}$ , $I_B = 60\text{ mA}$ ) ( $I_C = 6.0\text{ A}$ , $I_B = 0.6\text{ A}$ )	$V_{CE(sat)}$	– – – – –	– 0.045 0.085 – –	0.040 0.060 0.100 0.220 0.300	V
Base – Emitter Saturation Voltage (Note 4) ( $I_C = 1.0\text{ A}$ , $I_B = 0.1\text{ A}$ )	$V_{BE(sat)}$	–	–	0.900	V
Base – Emitter Turn-on Voltage (Note 4) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ )	$V_{BE(on)}$	–	–	0.900	V
Cutoff Frequency ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$f_T$	100	–	–	MHz
Input Capacitance ( $V_{EB} = 5.0\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	400	–	pF
Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	37	–	pF

**SWITCHING CHARACTERISTICS**

Delay ( $V_{CC} = 30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_d$	–	85	–	ns
Rise ( $V_{CC} = 30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_r$	–	115	–	ns
Storage ( $V_{CC} = 30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_s$	–	1350	–	ns
Fall ( $V_{CC} = 30\text{ V}$ , $I_C = 750\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_f$	–	125	–	ns

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .



**Figure 1. Power Derating**

# NSS60601MZ4

## TYPICAL CHARACTERISTICS

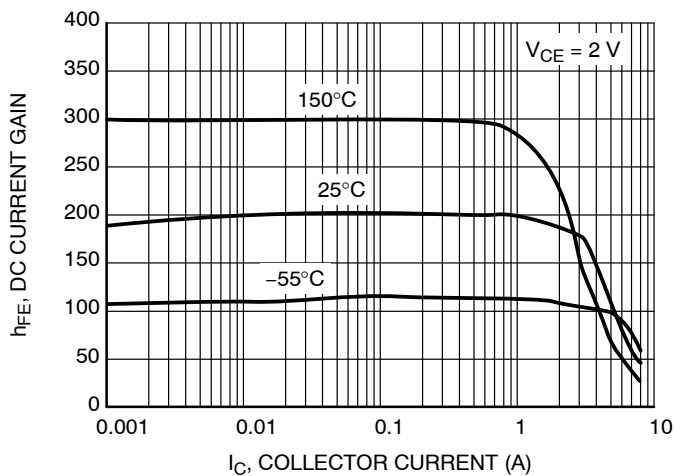


Figure 2. DC Current Gain

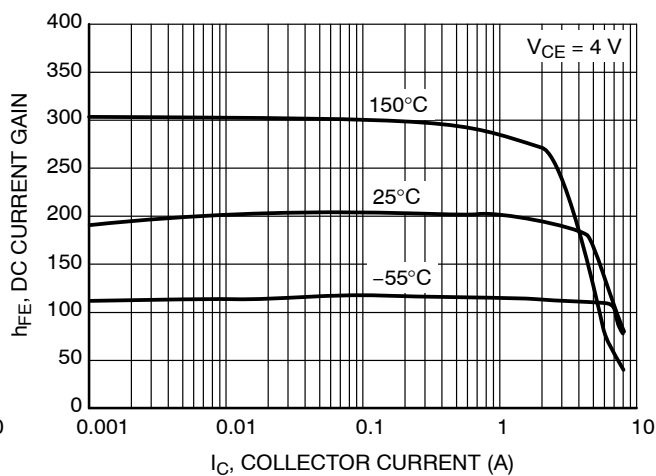


Figure 3. DC Current Gain

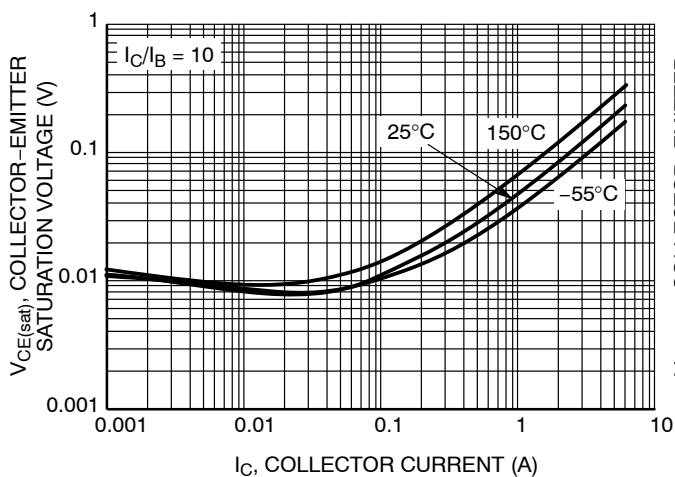


Figure 4. Collector-Emitter Saturation Voltage

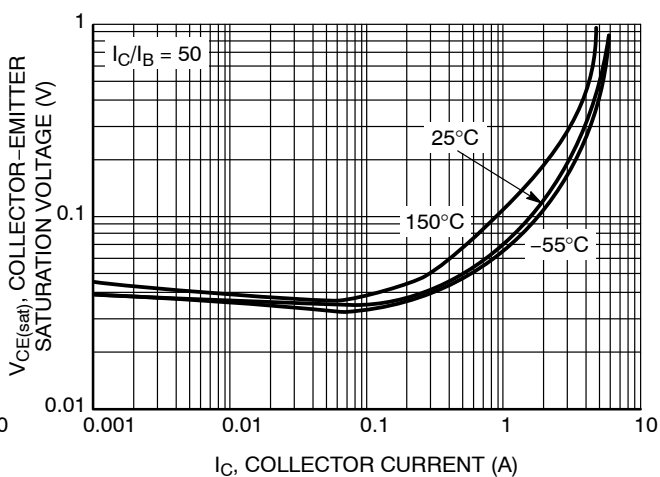


Figure 5. Collector-Emitter Saturation Voltage

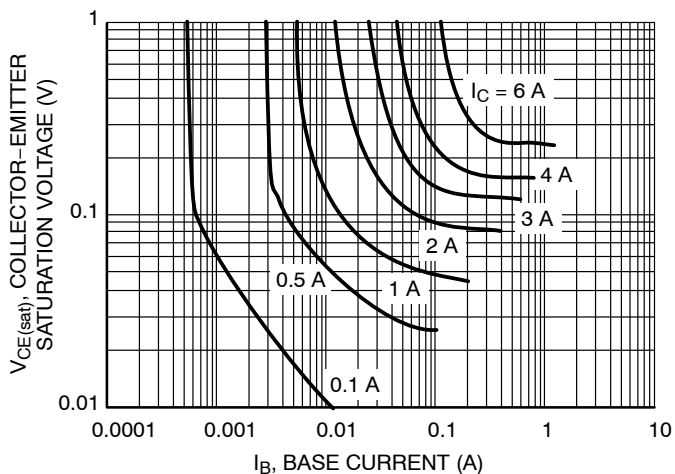


Figure 6. Collector Saturation Region

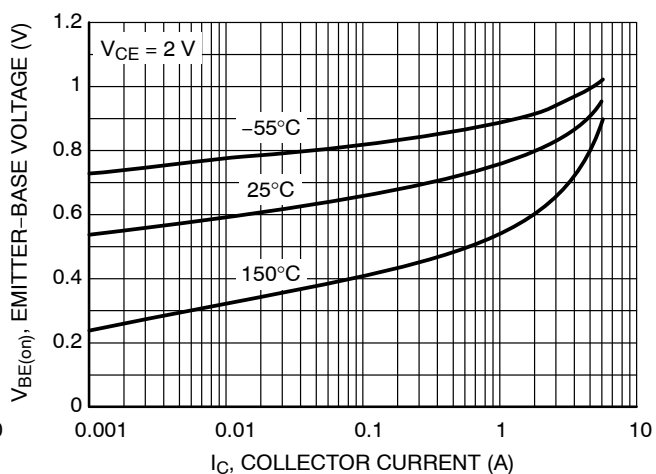


Figure 7.  $V_{BE(on)}$  Voltage

# NSS60601MZ4

## TYPICAL CHARACTERISTICS

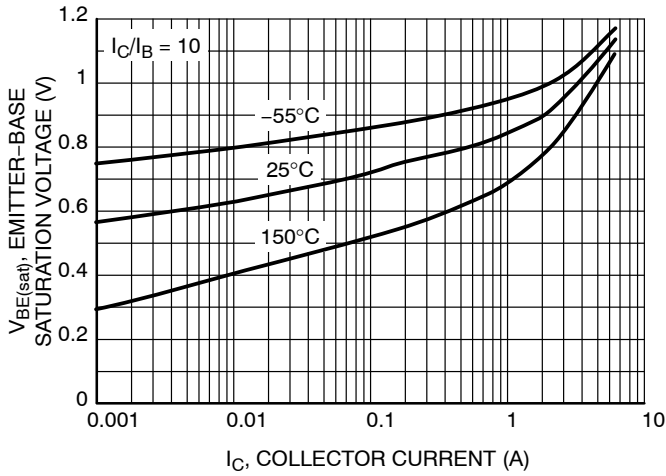


Figure 8. Base-Emitter Saturation Voltage

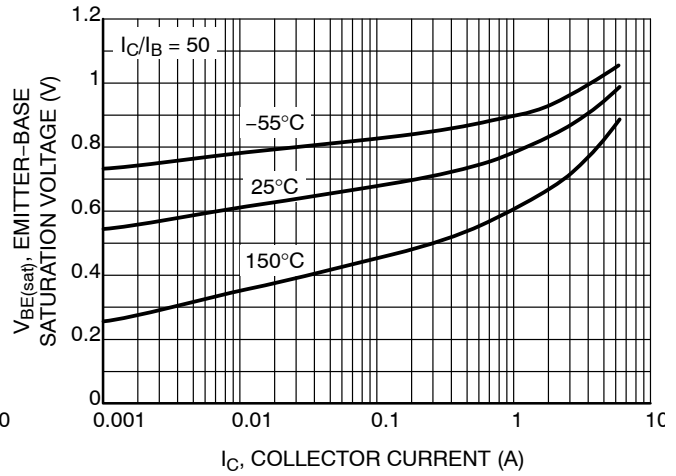


Figure 9. Base-Emitter Saturation Voltage

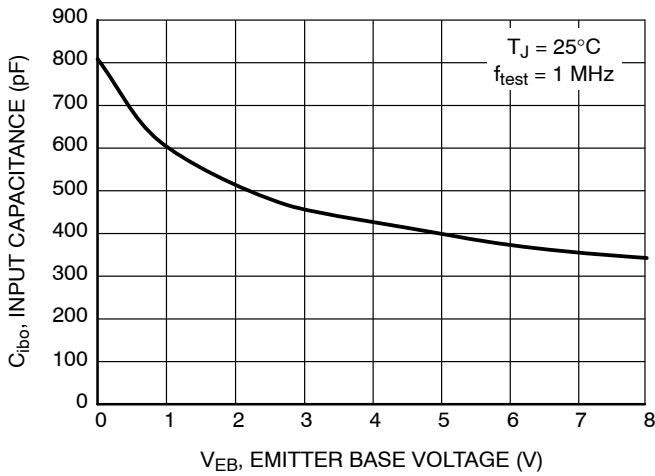


Figure 10. Input Capacitance

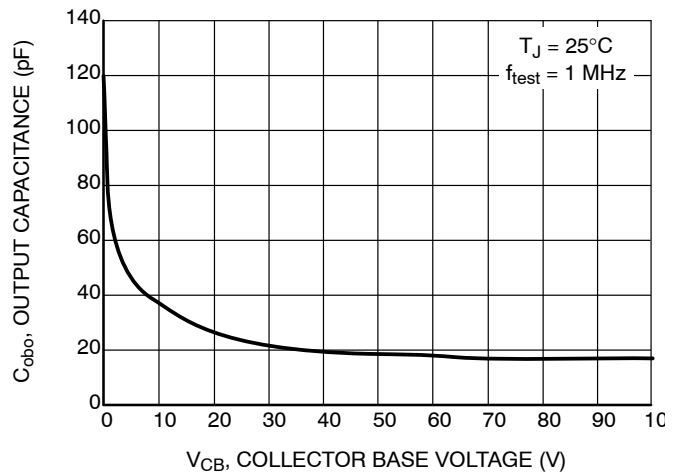


Figure 11. Output Capacitance

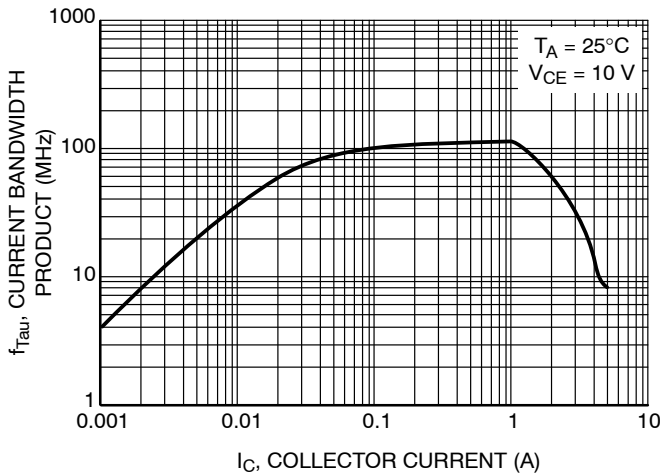


Figure 12. Current-Gain Bandwidth Product

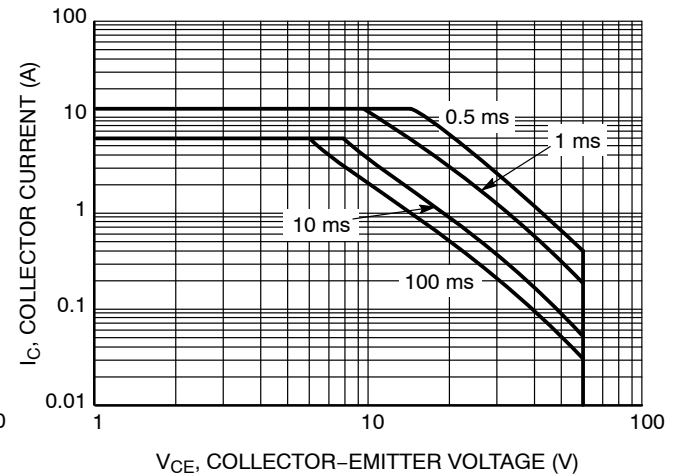


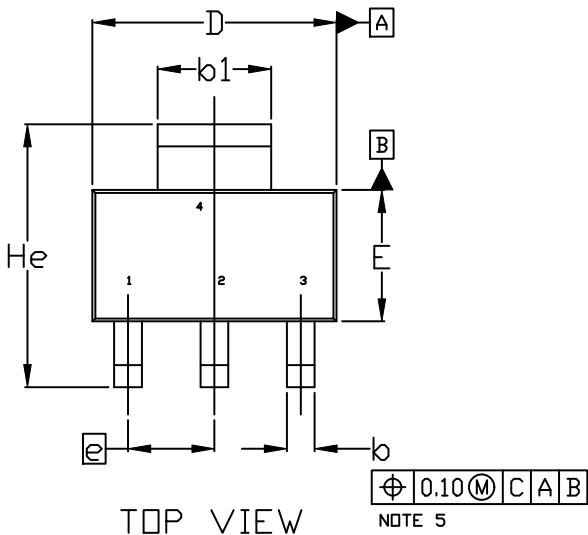
Figure 13. Safe Operating Area



SCALE 1:1

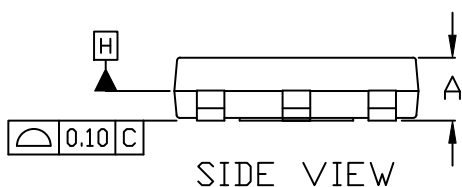
**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

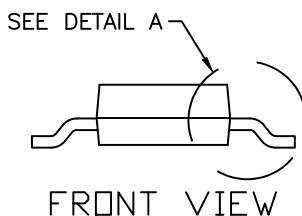


TOP VIEW

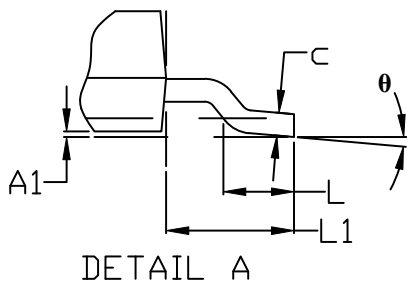
$\oplus 0.10 (M) C A B$   
NOTE 5



SIDE VIEW



FRONT VIEW

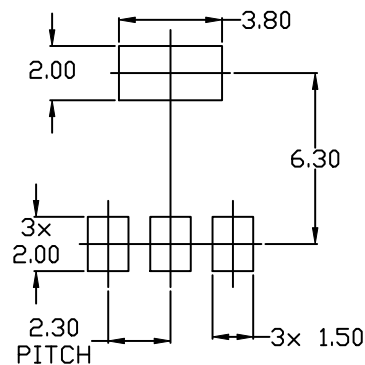


DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
$\theta$	0°	---	10°



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<b>DESCRIPTION:</b>	<b>SOT-223 (TO-261)</b>	<b>PAGE 1 OF 2</b>

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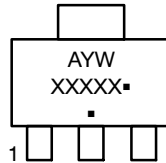


**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

- |  |   |   |   |   |
|--|---|---|---|---|
| <p>STYLE 1:<br/>                 PIN 1. BASE<br/>                 2. COLLECTOR<br/>                 3. EMITTER<br/>                 4. COLLECTOR</p> | <p>STYLE 2:<br/>                 PIN 1. ANODE<br/>                 2. CATHODE<br/>                 3. NC<br/>                 4. CATHODE</p>        | <p>STYLE 3:<br/>                 PIN 1. GATE<br/>                 2. DRAIN<br/>                 3. SOURCE<br/>                 4. DRAIN</p>           | <p>STYLE 4:<br/>                 PIN 1. SOURCE<br/>                 2. DRAIN<br/>                 3. GATE<br/>                 4. DRAIN</p>   | <p>STYLE 5:<br/>                 PIN 1. DRAIN<br/>                 2. GATE<br/>                 3. SOURCE<br/>                 4. GATE</p>    |
| <p>STYLE 6:<br/>                 PIN 1. RETURN<br/>                 2. INPUT<br/>                 3. OUTPUT<br/>                 4. INPUT</p>        | <p>STYLE 7:<br/>                 PIN 1. ANODE 1<br/>                 2. CATHODE<br/>                 3. ANODE 2<br/>                 4. CATHODE</p> | <p>STYLE 8:<br/>                 CANCELLED</p>  | <p>STYLE 9:<br/>                 PIN 1. INPUT<br/>                 2. GROUND<br/>                 3. LOGIC<br/>                 4. GROUND</p> | <p>STYLE 10:<br/>                 PIN 1. CATHODE<br/>                 2. ANODE<br/>                 3. GATE<br/>                 4. ANODE</p> |
| <p>STYLE 11:<br/>                 PIN 1. MT 1<br/>                 2. MT 2<br/>                 3. GATE<br/>                 4. MT 2</p>             | <p>STYLE 12:<br/>                 PIN 1. INPUT<br/>                 2. OUTPUT<br/>                 3. NC<br/>                 4. OUTPUT</p>         | <p>STYLE 13:<br/>                 PIN 1. GATE<br/>                 2. COLLECTOR<br/>                 3. EMITTER<br/>                 4. COLLECTOR</p> |   |   |

**GENERIC MARKING DIAGRAM\***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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